



#### 50V N-Channel Enhancement Mode MOSFET - ESD Protected

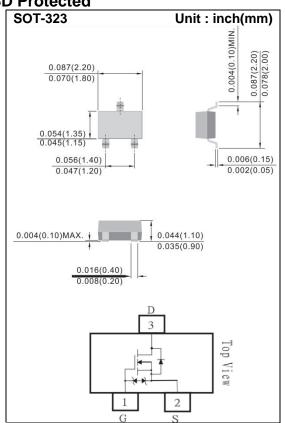
Voltage 50 V Current 360mA

#### **Features**

- RDS(ON), VGS@10V, ID@500mA<1.6Ω
- RDS(ON), VGS@4.5V, ID@200mA<2.5Ω</li>
- RDS(ON) , VGS@2.5V, ID@100mA<4.5Ω</li>
- Advanced Trench Process Technology
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

- Case: SOT-323 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00018 ounces, 0.005 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	50	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	360	mA
Pulsed Drain Current		I <sub>DM</sub>	1200	mA
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	236	mW
	Derate above 25°C		1.89	mW/°C
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55~150	°C
Typical Thermal resistance				
- Junction to Ambient (Note 3)		$R_{\theta JA}$	530	°C/W





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	50	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.8	1.0	1.5	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =500mA	-	0.96	1.6	Ω	
		V <sub>GS</sub> =4.5V,I <sub>D</sub> =200mA	-	1.25	2.5		
		V <sub>GS</sub> =2.5V,I <sub>D</sub> =100mA	-	2.73	4.5		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =50V, $V_{GS}$ =0V	-	0.01	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	<u>+</u> 3.0	<u>+</u> 10	uA	
Dynamic							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =25V, I <sub>D</sub> =250mA, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	0.63	1	nC	
Gate-Source Charge	$Q_gs$		-	0.2	-		
Gate-Drain Charge	$Q_gd$		-	0.23	-		
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	25	50	pF	
Output Capacitance	Coss		-	9.5	20		
Reverse Transfer Capacitance	Crss	I=1.UIVIDZ	-	2.1	5		
Switching							
Turn-On Delay Time	td <sub>(on)</sub>	)/ O5)/ L 500 ·· A	-	2.2	5		
Turn-On Rise Time	tr	V <sub>DD</sub> =25V, I <sub>D</sub> =500mA,		19.2	38	ns	
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}=10V$ , $R_{G}=6\Omega$ (Note 1,2)		6.2	12		
Turn-Off Fall Time	tf	R <sub>G</sub> =012	-	23	50		
Drain-Source Diode							
Maximum Continuous Drain-Source				_	500	mA	
Diode Forward Current	I <sub>S</sub>				300	IIIA	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =500mA, V <sub>GS</sub> =0V		0.86	1.5	V	

#### NOTES:

- 1. Pulse width < 300 μs, Duty cycle < 2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejua is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper





#### **TYPICAL CHARACTERISTIC CURVES**

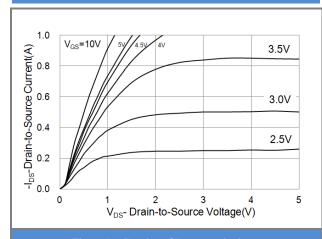
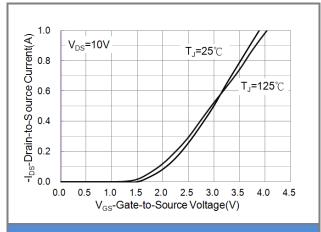


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

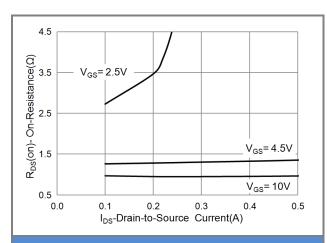


Fig.3 On-Resistance vs. Drain Current

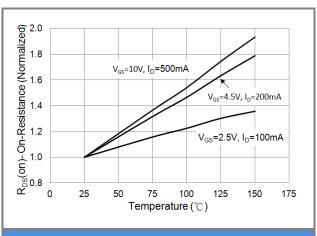


Fig.4 On-Resistance vs. Junction temperature

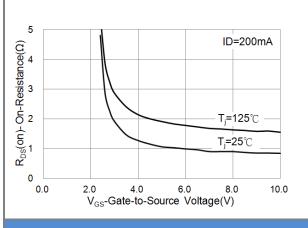


Fig.5 On-Resistance Variation with VGS.

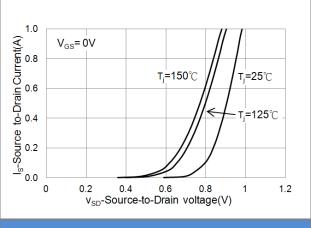


Fig.6 Body Dlode CharacterIslcs





#### **TYPICAL CHARACTERISTIC CURVES**

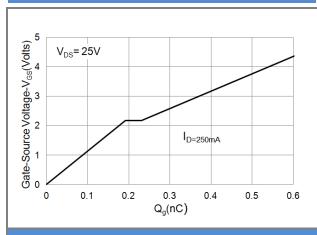


Fig.7 Gate-Charge Characteristics

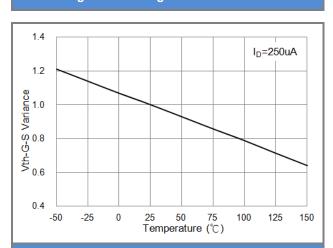


Fig.9 Threshold Voltage Variation with Temperature.

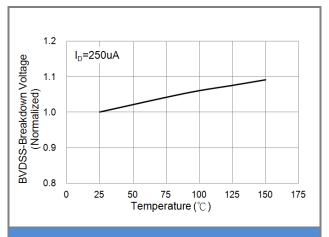


Fig.8 Breakdown Voltage Variation vs. Temperature

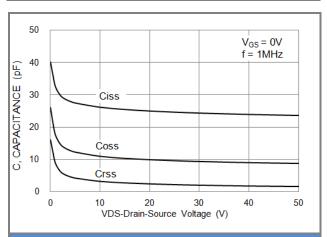


Fig.10 Capacitance vs. Drain-Source Voltage.

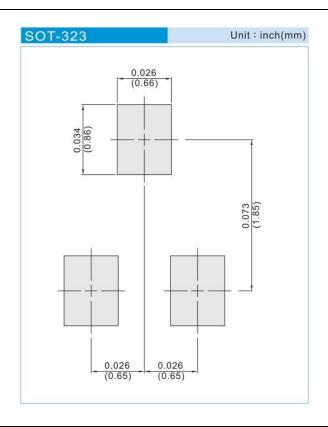




### PART NO PACKING CODE VERSION

PART NO PACKING  CODE VERSION	Package Type	Packing type	Marking	Version
PJC138K_R1_00001	SOT-323	3K pcs / 7" reel	8KW	Halogen free
PJC138K_R2_00001	SOT-323	12K pcs / 13" reel	8KW	Halogen free

### **MOUNTING PAD LAYOUT**







#### Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
  responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
  representation or warranty that such applications will be suitable for the specified use without further testing or
  modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

## Panjit:

PJC138K\_R1\_00001 PJC138K\_R2\_00001